

23. A gate stack, including a non-crystalline metallic silicide film.
24. (Previously Twice Amended) A gate stack, including an amorphous metallic silicide film wherein said metallic silicide film is substantially devoid of silicon clusters.
25. (Thrice Amended) A gate stack on a silicon substrate having a dielectric layer thereover, comprising:
  - a polysilicon layer disposed over said dielectric layer;
  - a non-crystalline metallic silicide film disposed over said polysilicon layer; and
  - a dielectric cap on said non-crystalline metallic silicide film.
26. (Twice Amended) A gate stack structure comprising a gate stack on a dielectric layer, over a silicon substrate, wherein said dielectric layer is substantially devoid of pitting.
27. (Amended) The gate stack structure of claim 26 wherein said gate stack includes a non-crystalline metallic silicide film.
28. (Previously Twice Amended) The gate stack structure of claim 26 wherein said gate stack includes an amorphous metallic silicide film substantially devoid of silicon clusters.